



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTY.'S DOCKET: 2001 P 14585 US

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In re the application of: )  
Chuan Lin )  
Serial No.: 10/059,321 ✓ )  
Filing Date: January 31, 2002 )  
Title: REDUCTION OF NEGATIVE BIAS )  
TEMPERATURE INSTABILITY IN )  
NARROW WIDTH PMOS USING F<sub>2</sub> )  
IMPLANTATION )

Group Art: 2812  
Examiner: I. Stanetta

Amendment Under 37 C.F.R. §1.116

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed October 16, 2002  
which rejected the claims in the above-identified patent  
application, applicant respectfully request reconsideration  
based upon the amendments hereinafter set forth.

A one month extension is requested and the fee therefor  
in the amount of \$110.00 is enclosed herewith as check number  
4617.

IN THE CLAIMS:

1. (Twice Amended) In a process of fabricating a narrow  
channel width PMOSFET device, the improvement of affecting  
reduction of negative bias temperature instability by use of  
F<sub>2</sub> side wall implantation [and subsequent high density plasma  
fill of a STI], comprising:

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